

Low Standby Power Offline Switching Power IC

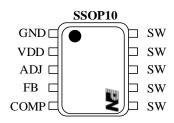
General description

The PN8085 consists of an integrated Current Mode Modulator controller and power MOSFET, specifically designed for a high performance off-line converter with minimal external components.

PWM, Burst-mode operation and low consumption device help to meet the standby energy saving standards and achieve higher efficiency. PN8085 can be designed for non-isolated flyback and Buck applications to meet different application requirements. Frequency modulation technology and Soft Driver technology fully guarantee good EMI performance.

The PN8085 offers complete protections including output over voltage protection, Cycle-by-Cycle current limiting (adjustable OCP), and OLP, and soft-start etc.

Package/Order Information



Ondon codo	Daalaaa	Typical Power		
Order code	Package	85~265V _{AC}		
PN8085ST-A1	SSOP10	5W		
PN8085LST-A1	SSOP10	5W		
PN8085HST-A1	SSOP10	5W		

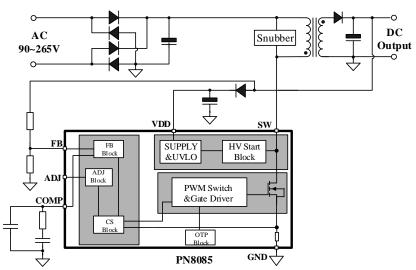
Features

- Internal 800V avalanche-rugged smart power VDMOSFET
- Non-isolated flyback and Buck applications PWM, Burst-mode
- Without startup resistance and CS detection resistance
- Internal HV Start-up Circuit, High and low voltage pin arranged on both sides to improve safety
- No-load consumption power < 30mW @230VAC
- Frequency modulation for low EMI
- VDD Operating voltage range 9~23V
- Excellent Protection Coverage:
 - ♦ Over Temperature Protection (OTP)
 - ♦ VDD Over Voltage Protection(OVP)
 - ♦ Cycle-by-Cycle Current Limiting (OCP)
 - ♦ Over load Protection(OLP)

Application

- Standby power supply
- Switch AC/DC
- White goods box power supply

Typical Circuit





Pin Definitions

Pin Name	Pin Number	Pin Function Description
GND	1	Ground
VDD	2	Power supply pin
ADJ	3	The overcurrent point is adjusted by the grounding resistance
FB	4	Flyback input pin
COMP	5	Error amplifier compensation
SW	6,7,8,9,10	Drain of the internal MOSFET

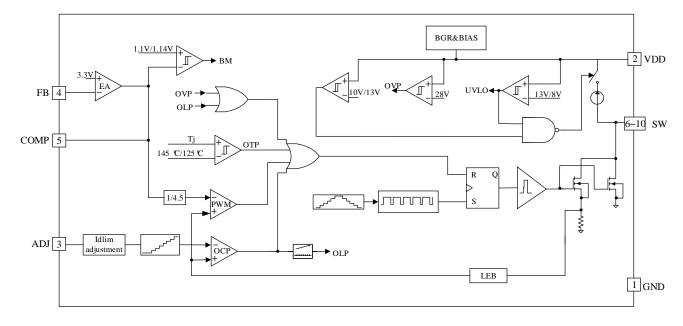
Typical Power

Part Number	Input Voltage	Adaptor ⁽¹⁾	Open Frame ⁽²⁾
DN10005	85~265V _{AC}	4W	5W
PN8085	$230V_{AC}$	6W	8W

Note:

- Typical practical continuous power is measured in closed environment at 50 $^{\circ}$ C ambient temperature. Typical practical continuous power is measured in opened environment at 50 $^{\circ}$ C ambient temperature.

Block Diagram





Absolute Maximum Ratings

Supply voltage Pin VDD	0.3~33V
Pin FB,ADJ,COMP	0.3~6.5V
High-Voltage Pin, SW	0.3~800V
Operating Junction Temperature	40~150 ℃
Storage Temperature Range	55~150 ℃

Note:

1. Test standard: ANSI/ESDA/JEDEC JS-001-2017.

Electrical Characteristics

(T_A= 25 °C, unless otherwise specified)

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Power Section	I	1			•	ı
Break-down voltage	BV _{DSS}	$I_{SW} = 250uA, T_J = 25 °C$	800	820		V
Off-state drain current	I _{OFF}	$V_{SW} = 650V, T_J = 25 ^{\circ}\text{C}$			100	uA
Drain-source on state resistance	R _{DS(on)}	$I_{SW} = 400 \text{mA}, T_J = 25 ^{\circ}\text{C}$		19		Ω
Supply Voltage Section						
VDD start up threshold	VDD _{on}		12	13	14	V
VDD under voltage shutdown threshold	$\mathrm{VDD}_{\mathrm{off}}$		7	8	9	V
V _{DD} clamp voltage	V _{CLAMP}		23	24.5	26	V
VDD over voltage protect	VDD_{ovp}		26.5	28	29.5	V
VDD self-powered charging voltage	VDD _{rech}		8.5	9.7	11	V
Time between restarts after protection	T _{RST}			1.1		s
Drain-source startup voltage	Vdrain_start		25		45	V
Supply Current Section						
Start up charging current	Ivdd_ch			-1.2		mA
self-powered charging current	Ivdd_rech			-9		mA
Operating supply current, switching	I _{VDD0}	V _{FB} =3.5V		1	1.5	mA
Operating supply current, under burst mode	I_{VDD1}	V _{FB} =0.5V		0.5	0.75	mA
Operating supply current, with protection tripping	Ivdd_Fault			0.6	0.9	mA
Oscillator Section						
Switching Frequency - PN8085				30		kHz
Switching Frequency - PN8085L	Fosc			60		kHz
Switching Frequency - PN8085H				115		kHz
Maximum duty cycle	D _{MAX}		75	80	85	%
Modulation frequency	FM			230		Hz
Frequency Variation	FD			±7		%



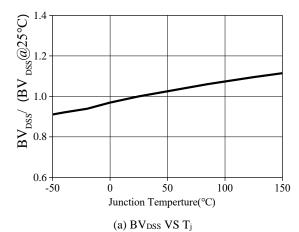
Electrical Characteristics

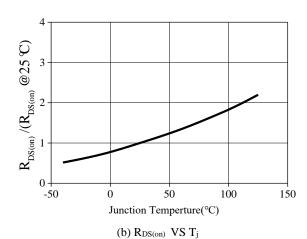
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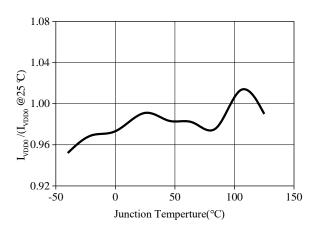
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT
FB Section	1					
EA reference voltage	V _{REF_EA}		3.2	3.3	3.4	V
FB pull on current	I_{FB_PULL}			1		uA
Trans conductance	Gm			2		mA/V
Error Amplifier Compensation	Section					
V _{COMP open} Loop Voltage	V _{COMP_OPEN}			5		V
COMP sink/source current	I _{COMP1}			0.15		mA
COMP short circuit current	I _{COMP2}			0.21		mA
Intermittent mode threshold voltage	V _{СОМР_ВМ_Н}			1.1		V
Intermittent mode hysteresis voltage	V _{COMP_BM_HYS}			40		mV
COMP impedance	R _{COMP}			25		kΩ
Current Sense Section						
Soft-start time	Tss			7.5		ms
Leading edge blanking time	T_{LEB}			450		ns
Drain current limit time	ID _{LIM}		0.32	0.35	0.38	A
OCP blanking time	Td_OCP			50		ms
Burst-mode drain current	ID_BM			0.085		A
Adjust Section						
ADJ open-circuit voltage	V _{ADJ_OPEN}			2		V
ADJ clamping voltage	V _{ADJ_CLP}			0.5		V
Thermal Section	<u>. </u>					•
Thermal shutdown temperature	T_{SD}		135	145		$\mathcal C$
Thermal shutdown hysteresis	T_{HYST}			20		\mathcal{C}

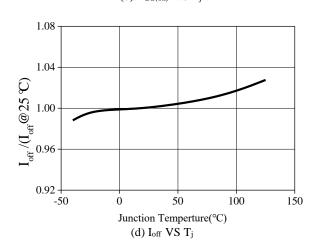


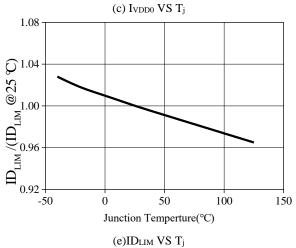
Typical Characteristics Plots













Functional Description

1. Startup

At start up, the internal high-voltage current source supplies the internal bias and charges the external VDD capacitor. When VDD reaches VDD_{on}, the device starts switching and the internal high-voltage current source stops charging the capacitor. After start up, the output to the VDD capacitor can be used to provide energy.

2. Soft-start up

In the process of startup, the current of drain increases to maximum limitation step by step. As a result, it can reduce the stress of secondary diode greatly and prevent the transformer turning into the saturation state. Typically, the duration of soft-start is 7.5ms.

3. Error Amplifier

The PN8085 internal integrated error amplifier samples the output voltage through the FB pin, and the FB pin voltage compares to the internal reference 3.3V (typical value). V_{COMP} is the voltage after error amplification, COMP needs an external compensation circuit to prevent loop oscillation.

4. Over current protection threshold adjustment

For some applications, ID_{LIM} may lead to high system overload protection power. In the case, ID_{LIM} can be reduced by adjust external resistance to the ground to match the requirements of the system.

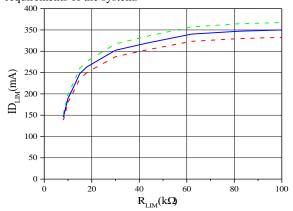


Fig.1 ID_{LIM} adjustment

5. Multi-mode work

PN8085 integrates PWM and burst-mode mixed modulation technologies to achieve ultra-low standby power consumption and the best efficiency in the full voltage rang.

At full load, PN8085 operates in PWM mode with a fixed oscillation frequency, and the operating frequency is Fosc.

The PN8085 enters burst-mode operation in order to minimize the power dissipation in standby mode. As the load decreases, the feedback voltage decreases. When the voltage on comp pin falls below $V_{\text{COMP_BM_L}}$, the device enters burst mode and power MOSFET stops switching. It can be

switched on again once the voltage on COMP pin exceeds $V_{\text{COMP_BM}} + V_{\text{COMP_BM_HYS}}.$

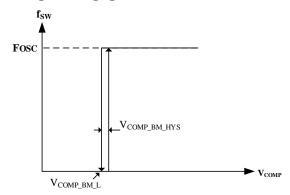


Fig.2 Fosc VS Vcomp

6. Over load protection (OLP)

Over load is defined as the load current exceeding a pre-set level due to an accident event as a fault. MOSFET current is the over-current protection threshold and meets the delay time of 50ms, the overload protection is triggered.

7. Over temperature protection (OTP)

The power MOSFET and control chip are integrated, making it easier for control chip to detect the temperature of MOSFET. If the temperature exceeds about 145 $^{\circ}$ C, OTP fault is activated. OTP is self-recovered when the temperature falls below 125 $^{\circ}$ C.

8. Error state timing self-recovery function

When VDD overvoltage, overload protection or over temperature protection occurs on the chip, PWM will turn off for 1.1s, VDD will open the self-supply circuit to maintain VDD voltage. After 1.1s, PN8085 redetects whether the error state is resolved. By shutting down the system for 1S after the error state, the power consumption of the error state can be effectively reduced.

9. Gate driver

The internal power MOSFET in PN8085 driven by a dedicated gate driver for power switch control. A good tradeoff is achieved through the built-in totem pole gate design with proper output strength and dead time. The good EMI system design and low idle loss is easier to achieve with this dedicated control scheme.



Typical Application

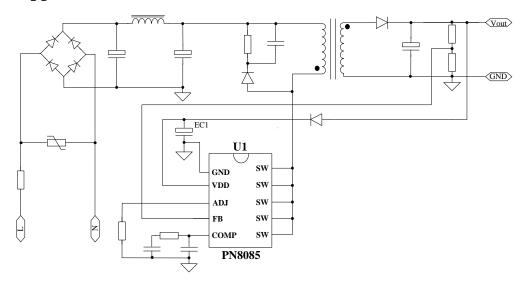


Fig.3 non-isolated fiyback application

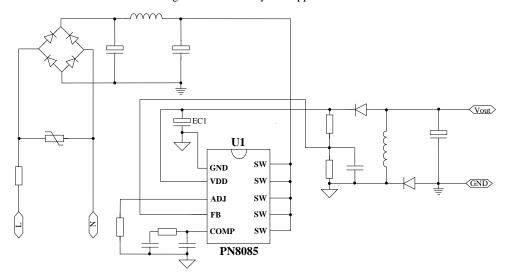


Fig.4 Buck system

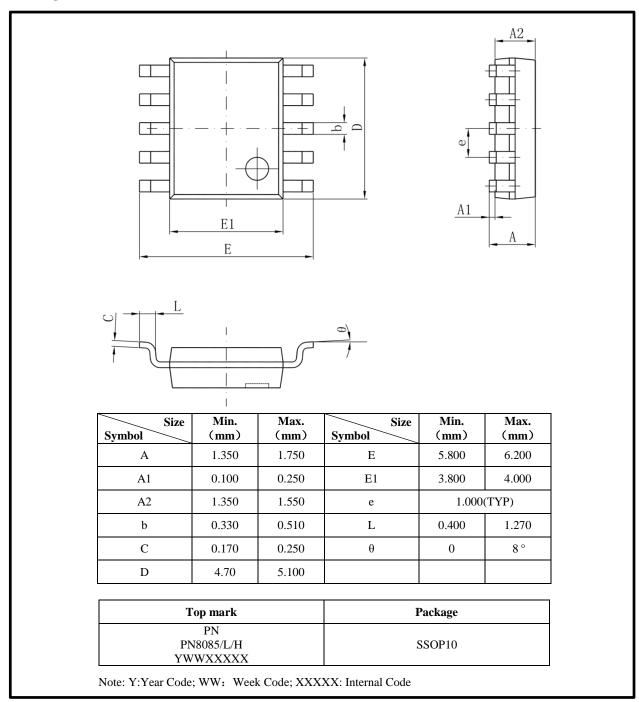
Component Parameter and Layout Considerations:

- 1. VDD capacitor EC1 should be placed at the nearest place between the VDD pin and the GND pin.
- 2. The line from PN8085 GND pin to the input electrolytic capacitor need to as short as possible



Package Information

Package Information SSOP10

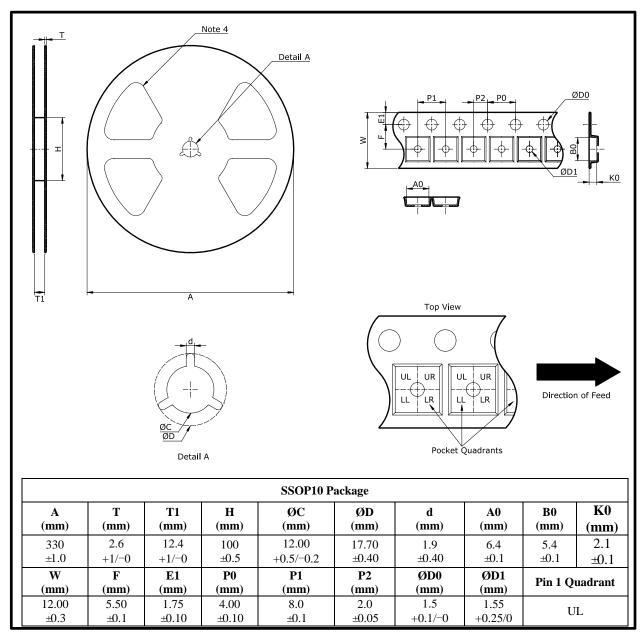


Notes:

- 1. This drawing is subjected to change without notice.
- 2. Body dimensions do not include mold flash or protrusion.



Tape and Reel Information



Notes:

- 1. This drawing is subjected to change without notice.
- 2. All dimensions are nominal and in mm.
- 3. This drawing is not in scale and for reference only. Customer can contact Chipown sales representative for further details.
- 4. The number of flange openings depends on the reel size and assembly site. This drawing shows an example only.



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